

## Features

- N-Channel MOSFET
- Low On-Resistance
- Very Low Gate Threshold Voltage, 1.2V max
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Ultra-Small Surface Mount Package
- ESD Protected Gate
- **Lead Free By Design/RoHS Compliant (Note 2)**
- **"Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

## Mechanical Data

- Case: DFN1006H4-3
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminal Connections: See Diagram
- Terminals: Finish – NiPdAu over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Marking Information: See Page 3
- Ordering Information: See Page 3
- Weight: 0.001 grams (approximate)

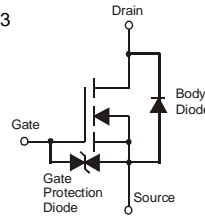


ESD PROTECTED



BOTTOM VIEW

DFN1006H4-3



Equivalent Circuit



TOP VIEW

## Maximum Ratings @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Drain Source Voltage	V <sub>DSS</sub>	30	V
Gate-Source Voltage	V <sub>GSS</sub>	±10	V
Drain Current (Note 1)	I <sub>D</sub>	300	mA

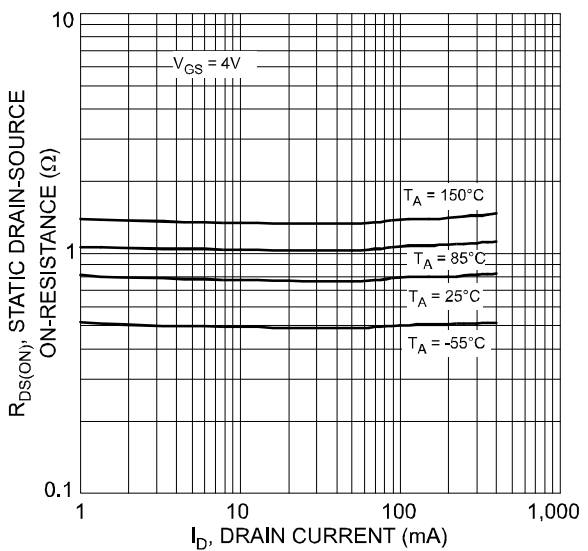
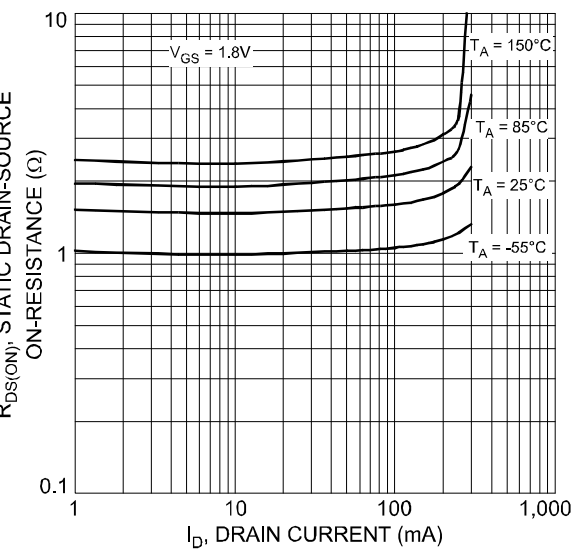
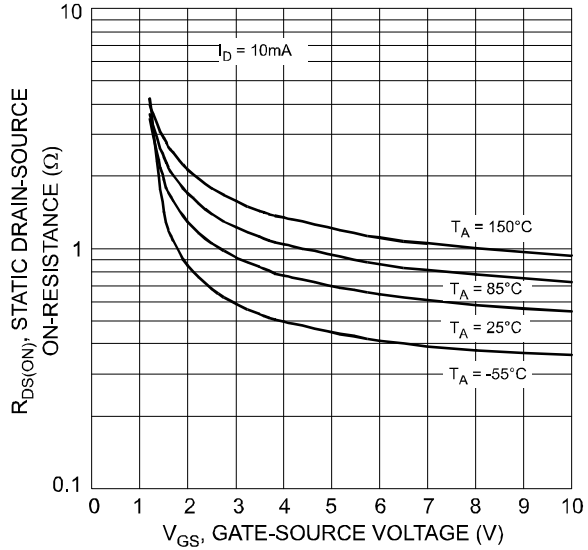
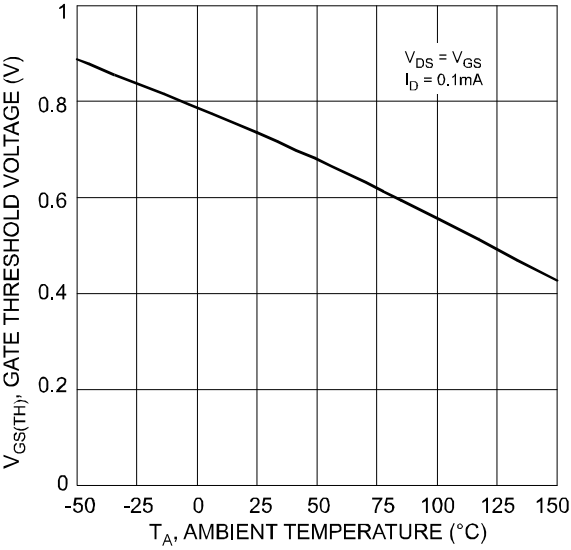
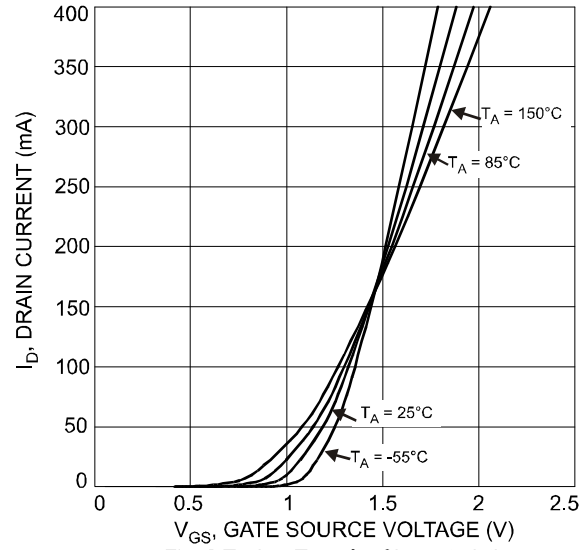
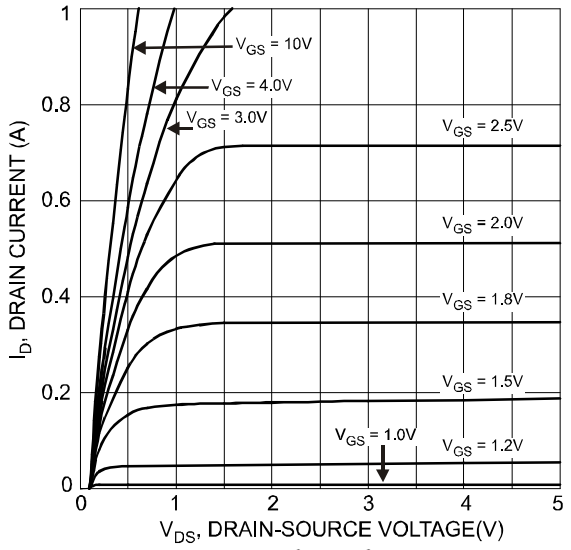
## Thermal Characteristics @T<sub>A</sub> = 25°C unless otherwise specified

Total Power Dissipation (Note 1) @T <sub>A</sub> = 25°C	P <sub>D</sub>	350	mW
Thermal Resistance, Junction to Ambient (Note 1)	R <sub>θJA</sub>	357	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

## Electrical Characteristics @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 4)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	30	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 10μA
Zero Gate Voltage Drain Current @ T <sub>C</sub> = 25°C	I <sub>DSS</sub>	—	—	1	μA	V <sub>DS</sub> = 30V, V <sub>GS</sub> = 0V
Gate-Body Leakage	I <sub>GSS</sub>	—	—	±10 ±500	μA nA	V <sub>GS</sub> = ±10V, V <sub>DS</sub> = 0V V <sub>GS</sub> = ±5V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS (Note 4)</b>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	0.6	—	1.2	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	—	—	2.2 1.5 1.2	Ω	V <sub>GS</sub> = 1.8V, I <sub>D</sub> = 20mA V <sub>GS</sub> = 2.5V, I <sub>D</sub> = 20mA V <sub>GS</sub> = 4.0V, I <sub>D</sub> = 100mA
Forward Transconductance	Y <sub>fs</sub>	100	—	—	mS	V <sub>DS</sub> = 10V, I <sub>D</sub> = 0.1A
Source-Drain Diode Forward Voltage	V <sub>SD</sub>	0.5	—	1.4	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 115mA
<b>DYNAMIC CHARACTERISTICS</b>						
Input Capacitance	C <sub>iss</sub>	—	39	—	pF	V <sub>DS</sub> = 3V, V <sub>GS</sub> = 0V f = 1.0MHz
Output Capacitance	C <sub>oss</sub>	—	10	—	pF	
Reverse Transfer Capacitance	C <sub>rss</sub>	—	3.6	—	pF	
Switching Time	Turn-on Time	t <sub>on</sub>	—	11	nS	V <sub>DD</sub> = 5V, I <sub>D</sub> = 10 mA, V <sub>GS</sub> = 0-5V
	Turn-off Time	t <sub>off</sub>	—	51	nS	

- Notes:
1. Device mounted on FR-4 PCB, pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at <http://www.diodes.com/datasheets/ap02001.pdf>.
  2. No purposefully added lead.
  3. Diodes Inc.'s "Green" policy can be found on our website at [http://www.diodes.com/products/lead\\_free/index.php](http://www.diodes.com/products/lead_free/index.php).
  4. Short duration pulse test used to minimize self-heating effect.



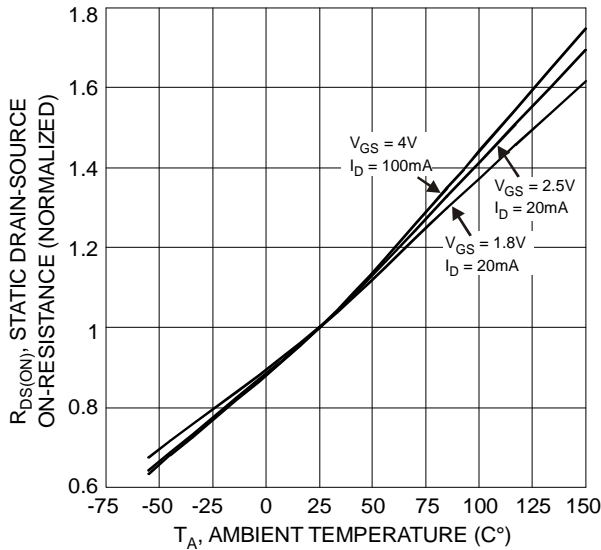


Fig. 7 Normalized Static Drain-Source On-Resistance vs. Ambient Temperature

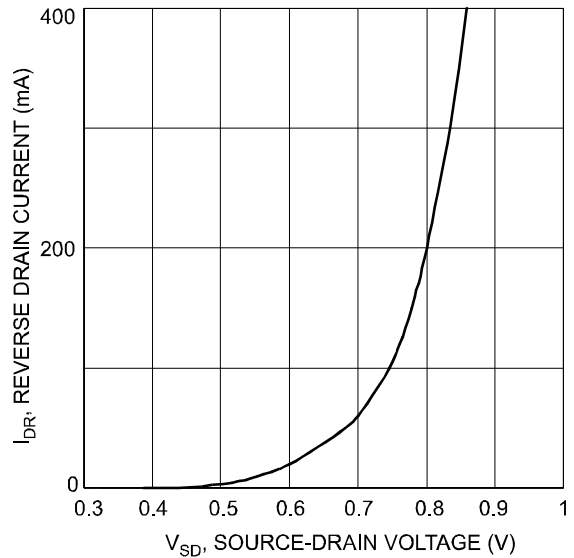


Fig. 8 Reverse Drain Current vs. Source-Drain Voltage

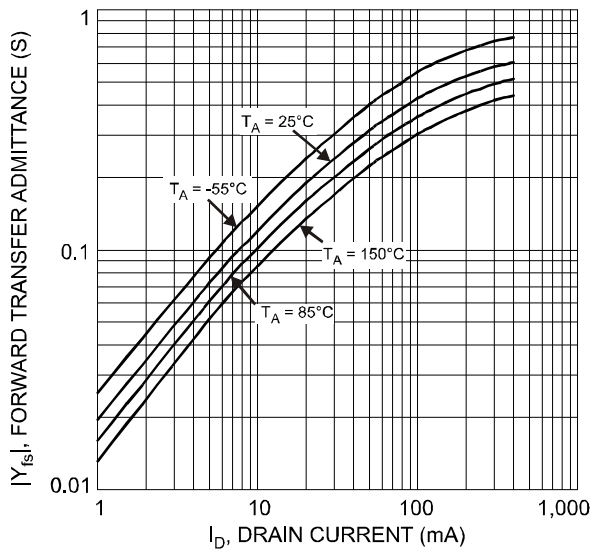


Fig. 9 Forward Transfer Admittance vs. Drain Current

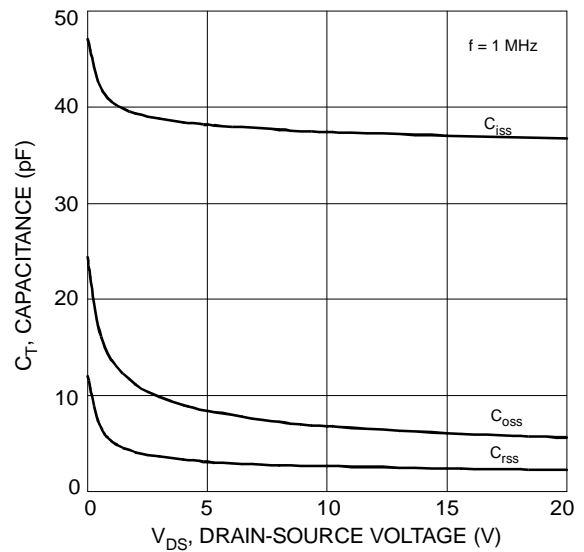


Fig. 10 Typical Capacitance

**Ordering Information** (Note 5)

Part Number	Case	Packaging
DMN32D2LFB4-7	DFN1006H4-3	3000/Tape & Reel

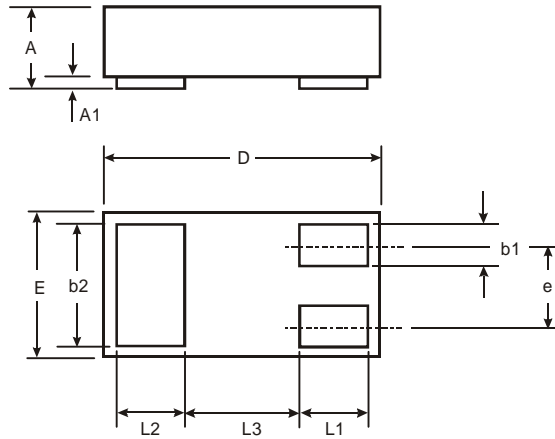
Notes: 5. For packaging details, go to our website at <http://www.diodes.com/datasheets/ap02007.pdf>.

**Marking Information**



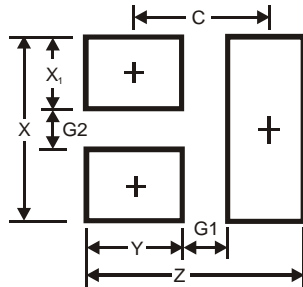
DV = Product Type Marking Code

**Package Outline Dimensions**



DFN1006H4-3			
Dim	Min	Max	Typ
A	—	0.40	—
A1	0	0.05	0.02
b1	0.10	0.20	0.15
b2	0.45	0.55	0.50
D	0.95	1.075	1.00
E	0.55	0.675	0.60
e	—	—	0.35
L1	0.20	0.30	0.25
L2	0.20	0.30	0.25
L3	—	—	0.40
All Dimensions in mm			

**Suggested Pad Layout**



Dimensions	Value (in mm)
Z	1.1
G1	0.3
G2	0.2
X	0.7
X1	0.25
Y	0.4
C	0.7

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